Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | 20 | V |
| V _{GS} | gate-source voltage | | | -8 | - | 8 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | - | 1 | Α |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 4.5 V; I_D = 500 mA; T_j = 25 °C | | - | 290 | 380 | mΩ |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1 | G | gate | 1 | D I |
| 2 | S | source | 2 🔲 📗 3 | |
| 3 | D | drain | Transparent top view DFN1006-3 (SOT883) | G S 017aaa255 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | | |
|-------------|-----------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| PMZ290UNE | DFN1006-3 | DFN1006-3: leadless ultra small plastic package; 3 solder lands | SOT883 | | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMZ290UNE | ZS |

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Limiting values

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------------|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 20 | V |
| V _{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | 1 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 625 | mA |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs | | - | 4 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 360 | mW |
| | | | [1] | - | 715 | mW |
| | | T _{sp} = 25 °C | | - | 2700 | mW |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | ain diode | | ' | | | , |
| Is | source current | T _{amb} = 25 °C | [1] | - | 680 | mA |
| ESD maxin | num rating | 1 | - | 1 | 1 | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [3] | - | 2000 | V |

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm². Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

Measured between all pins.

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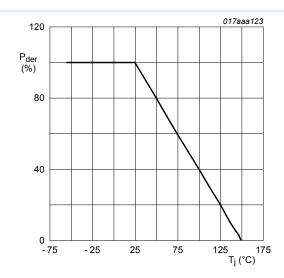


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

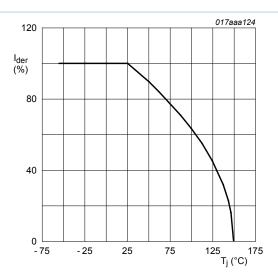
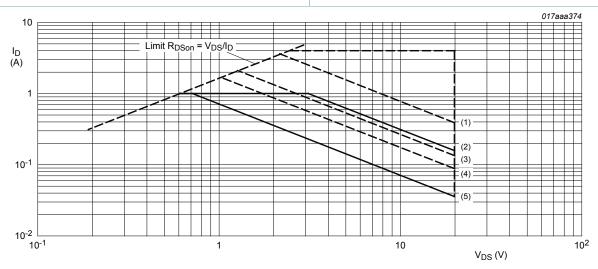


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



 I_{DM} = single pulse

- $(1) t_p = 1 ms$
- (2) DC; T_{sp} = 25 °C
- (3) $t_0 = 10 \text{ ms}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | [1] | - | 305 | 360 | K/W |
| | | | [2] | - | 150 | 175 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 40 | K/W |

- 1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

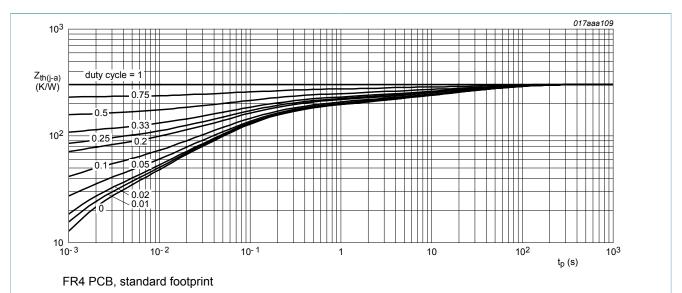


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

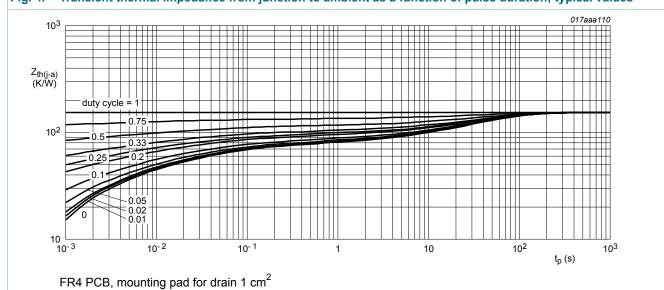


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7 Characteristics

| Table 7. Symbol | Characteristics Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-------------------------------|---|------|------|------|---------|
| | aracteristics | | | .76 | max | - Ornic |
| | drain-source | I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C | 20 | | | V |
| V _{(BR)DSS} | breakdown voltage | ID - 230 μA, VGS - 0 V, I _j - 25 C | 20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 0.5 | 0.75 | 0.95 | V |
| I_{DSS} | drain leakage current | $V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | 1 | μA |
| | | V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 10 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μA |
| | | V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μA |
| | | V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 500 | nA |
| | | V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 500 | nA |
| R _{DSon} | drain-source on-state | V _{GS} = 4.5 V; I _D = 500 mA; T _j = 25 °C | - | 290 | 380 | mΩ |
| resist | resistance | V _{GS} = 4.5 V; I _D = 500 mA; T _j = 150 °C | - | 460 | 610 | mΩ |
| | | V_{GS} = 2.5 V; I_D = 400 mA; T_j = 25 °C | - | 420 | 620 | mΩ |
| | | V _{GS} = 1.8 V; I _D = 100 mA; T _j = 25 °C | - | 600 | 1100 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C | - | 1.6 | - | S |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 10 V; I _D = 500 mA; V _{GS} = 4.5 V; | - | 0.45 | 0.68 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 0.15 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.15 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; | - | 55 | 83 | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 15 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 7 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 10 V; R_L = 250 Ω ; V_{GS} = 4.5 V; | - | 6 | 12 | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$ | - | 4 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 86 | 172 | ns |
| t _f | fall time | | - | 31 | - | ns |
| Source-d | rain diode | | ı | 1 | - | |
| V_{SD} | source-drain voltage | $I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | 0.48 | 0.77 | 1.2 | V |

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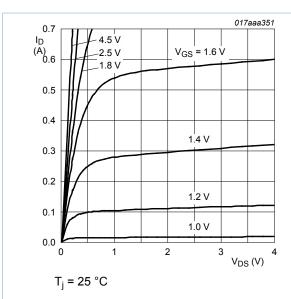
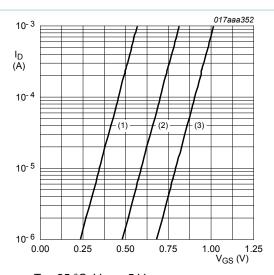


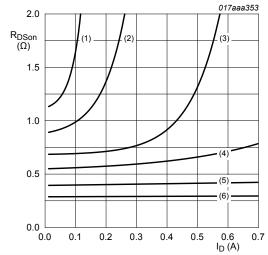
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 T_i = 25 °C; V_{DS} = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



T_i = 25 °C

(1) $V_{GS} = 1.3 \text{ V}$

(2) $V_{GS} = 1.4 \text{ V}$

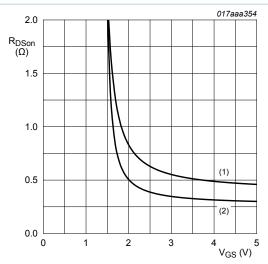
 $(3) V_{GS} = 1.6 V$

 $(4) V_{GS} = 1.8 V$

 $(5) V_{GS} = 2.5 V$

 $(6) V_{GS} = 4.5 V$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



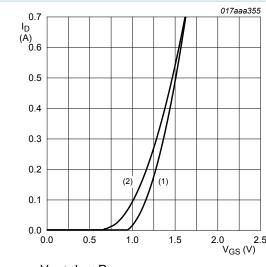
 $I_D = 400 \text{ mA}$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ (1) $T_i = 25 \, ^{\circ}C$

(2) $T_i = 150 \, ^{\circ}\text{C}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

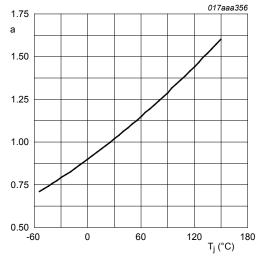
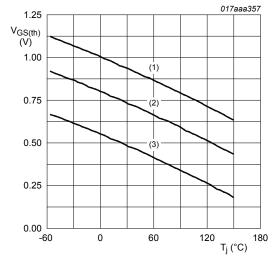


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

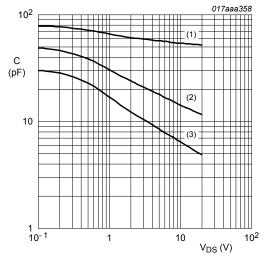
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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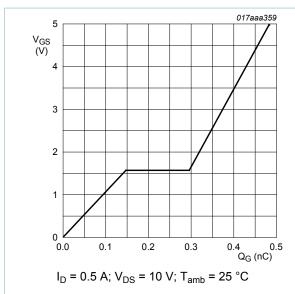


Fig. 14. Gate-source voltage as a function of gate charge; typical values

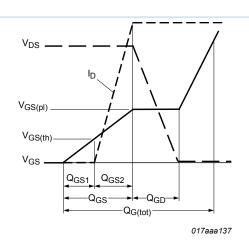
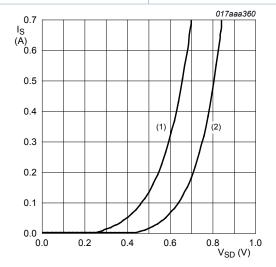


Fig. 15. Gate charge waveform definitions



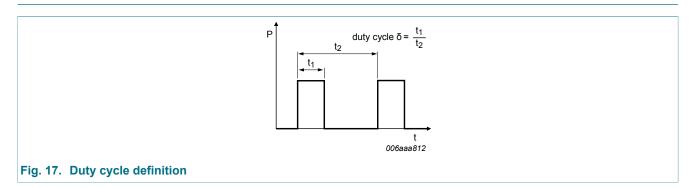
 $V_{GS} = 0 V$ (1) $T_j = 150 \, ^{\circ}C$

(2) $T_i = 25 \,^{\circ}\text{C}$

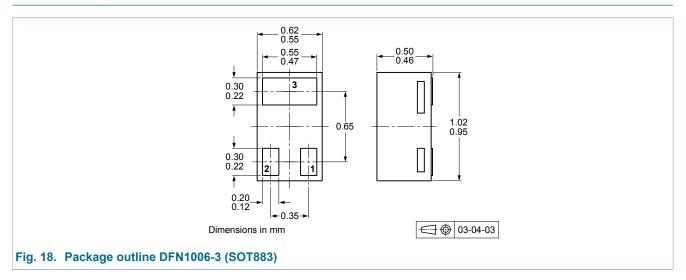
Fig. 16. Source current as a function of source-drain voltage; typical values

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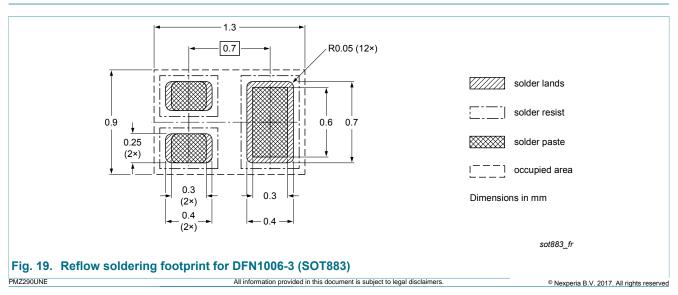
11. Test information



12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMZ290UNE v.1 | 20140514 | Product data sheet | - | - |

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|--------------------------------------|--------------------|---|
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